

# GTM CORPORATION

ISSUED DATE :2003/12/15  
REVISD DATE :2004/11/29B

## GPN2907A PNP EPITAXIAL PLANAR TRANSISTOR

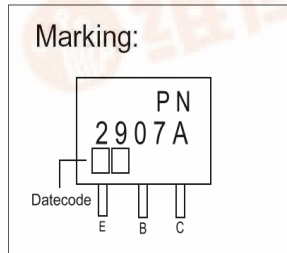
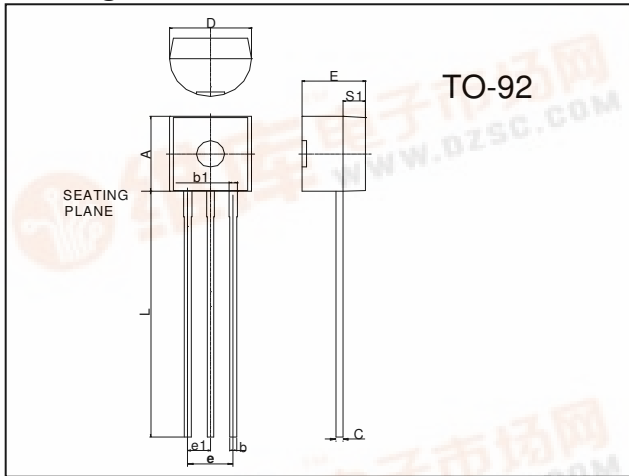
### Description

The GPN2907A is designed for general purpose amplifier and high speed, medium-power switching applications

### Features

- \*Low Collect Saturation voltage.
- \*High Speed Switching.
- \*For Complementary Use with NPN Type GPN2222A.

### Package Dimensions



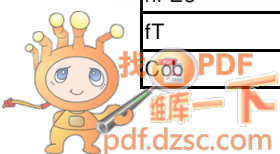
| REF. | Millimeter |      | REF. | Millimeter |       |
|------|------------|------|------|------------|-------|
|      | Min.       | Max. |      | Min.       | Max.  |
| A    | 4.45       | 4.7  | D    | 4.44       | 4.7   |
| S1   | 1.02       | -    | E    | 3.30       | 3.81  |
| b    | 0.36       | 0.51 | L    | 12.70      | -     |
| b1   | 0.36       | 0.76 | e1   | 1.150      | 1.390 |
| C    | 0.36       | 0.51 | e    | 2.42       | 2.66  |

### Absolute Maximum Ratings at Ta = 25°C

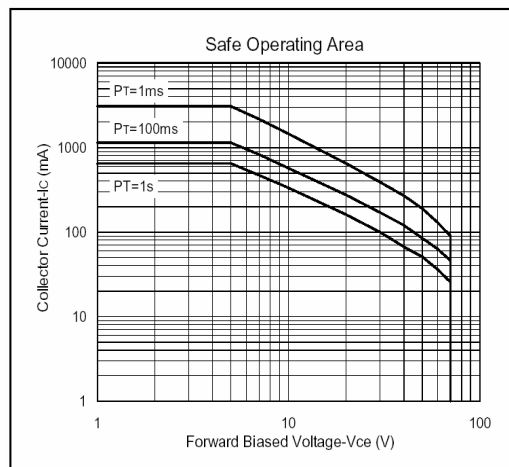
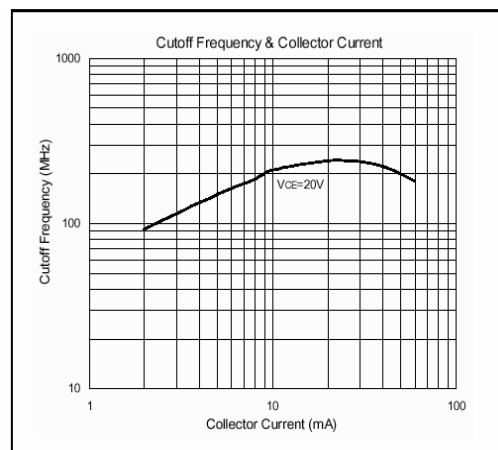
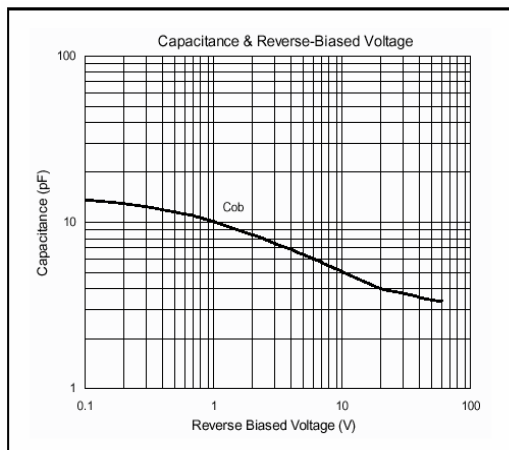
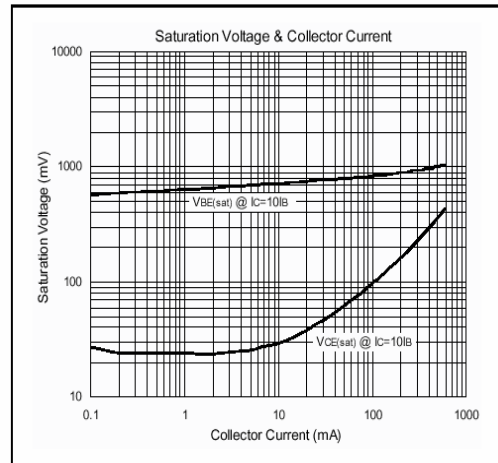
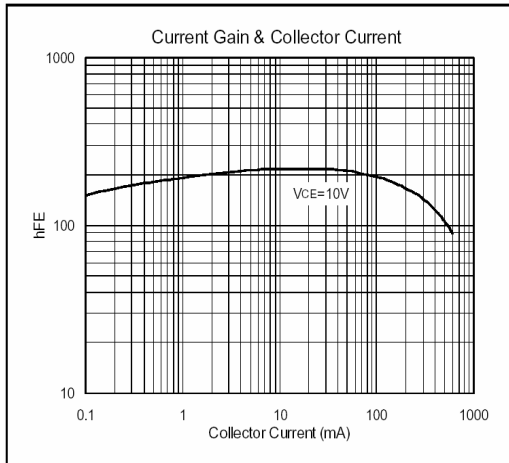
| Parameter                    | Symbol | Ratings    | Unit |
|------------------------------|--------|------------|------|
| Junction Temperature         | Tj     | +150       | °C   |
| Storage Temperature          | Tstg   | -55 ~ +150 | °C   |
| Collector to Base Voltage    | VCBO   | -60        | V    |
| Collector to Emitter Voltage | VCEO   | -60        | V    |
| Emitter to Base Voltage      | VEBO   | -5         | V    |
| Collector Current            | IC     | -600       | mA   |
| Total Power Dissipation      | Pd     | 625        | mW   |

### Electrical Characteristics at Ta = 25°C

| Symbol    | Min. | Typ. | Max. | Unit | Test Conditions              |
|-----------|------|------|------|------|------------------------------|
| BVCBO     | -60  | -    | -    | V    | IC=-10uA, IE=0               |
| BVCEO     | -60  | -    | -    | V    | IC=-10mA, IB=0               |
| BVEBO     | -5   | -    | -    | V    | IC=-10uA, IC=0               |
| ICBO      | -    | -    | -10  | nA   | VCB=-50V, IC=0               |
| ICEX      | -    | -    | -50  | nA   | VCE-30V, VBE=-0.5            |
| VCE(sat)1 | -    | -0.2 | -0.4 | V    | IC=-150mA, IB=-15mA          |
| VCE(sat)2 | -    | -0.5 | -1.6 | V    | IC=-500mA, IB=-50mA          |
| VBE(sat)1 | -    | -    | -1.3 | V    | IC=-150mA, IB=-15mA          |
| VBE(sat)2 | -    | -    | -2.6 | V    | IC=-500mA, IB=-50mA          |
| hFE1      | 75   | -    | -    | -    | VCE=-10V, IC=-100uA          |
| hFE2      | 100  | -    | -    | -    | VCE=-10V, IC=-1mA            |
| hFE3      | 100  | -    | -    | -    | VCE=-10V, IC=-10mA           |
| hFE4      | 100  | 180  | 300  | -    | VCE=-10V, IC=-150mA          |
| hFE5      | 50   | -    | -    | -    | VCE=-10V, IC=-500mA          |
| fT        | 200  | -    | -    | MHZ  | VCE=-20V, IC=-50mA, f=100MHZ |
|           | -    | -    | 8    | pF   | VCB=-10V, F=1MHZ             |



## Characteristics Curve



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